



30V N-Channel MOSFET



SOT-23

Pin Definition:



- Gate
 Source
- 3. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)	
30	57 @ V _{GS} =10V	3.5	
	94 @ V _{GS} =4.5V	2.8	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

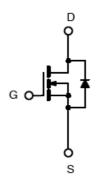
- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM2306CX RFG	SOT-23	3Kpcs / 7" Reel

Note: "G" denote for Green Product

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	r Symbol			Unit	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current		I _D	3.5	А	
Pulsed Drain Current	ed Drain Current		±20	А	
Continuous Source Current (Diode C	Conduction) ^{a,b}	Is	1.7	Α	
	Ta = 25°C	1	1.25	W	
Maximum Power Dissipation	Ta = 75°C	P _D	0.8		
Operating Junction Temperature	perating Junction Temperature		+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit			
Junction to Case Thermal Resistance	$R\Theta_{JC}$	75	°C/W			
Junction to Ambient Thermal Resistance (PCB mounted)	R⊖ _{JA}	130	°C/W			

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Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.



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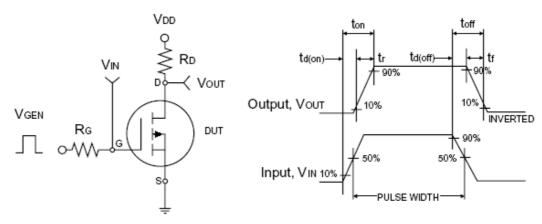


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1		3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$	I _{DSS}			1.0	μΑ
On-State Drain Current	$V_{DS} \ge 4.5 V, V_{GS} = 10 V$	I _{D(ON)}	6			Α
Drain Course On State Besistance	$V_{GS} = 10V, I_D = 3.5A$			46	57	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 2.8A$	R _{DS(ON)}		70	94	
Forward Transconductance	$V_{DS} = 15V, I_{D} = 3.5A$	g_{fs}	1	11		S
Diode Forward Voltage	$I_S = 1.7A, V_{GS} = 0V$	V_{SD}	1	-1	1.2	V
Dynamic ^b						
Total Gate Charge	\/ 45\/ L 0.5A	Q_g		4.2	7	
Gate-Source Charge	$V_{DS} = 15V, I_D = 3.5A,$	Q_{gs}		1.9		nC
Gate-Drain Charge	V _{GS} = 10V	Q_{gd}		1.35		
Input Capacitance	\/ 45\/ \/ 0\/	C _{iss}	-	555		
Output Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$	C _{oss}	1	120		pF
Reverse Transfer Capacitance	f = 1.0MHz	C_{rss}		60		
Switching ^c						
Turn-On Delay Time	\/ 45\/ D 450	t _{d(on)}		4.2	5.5	
Turn-On Rise Time	$V_{DD} = 15V, R_{L} = 15\Omega,$	t _r		19	25	~C
Turn-Off Delay Time	$I_D = 1A, V_{GEN} = 10V,$	t _{d(off)}		13	17	nS
Turn-Off Fall Time	$R_G = 6\Omega$	t _f		9	12	

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
 b. For DESIGN AID ONLY, not subject to production testing.
 b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms



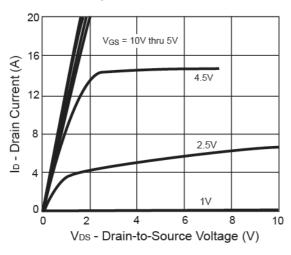
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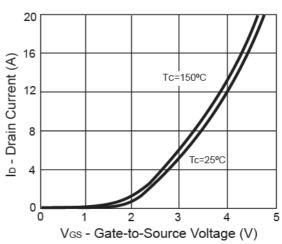


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

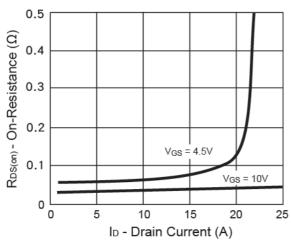
Output Characteristics



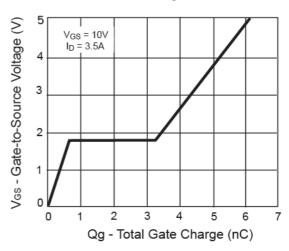
Transfer Characteristics



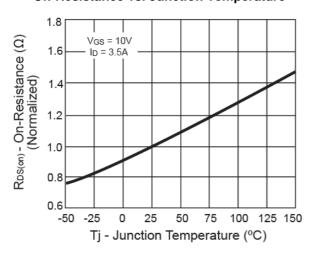
On-Resistance vs. Drain Current



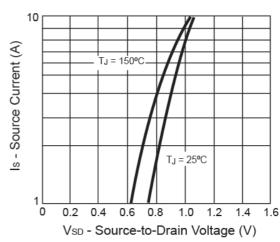
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage





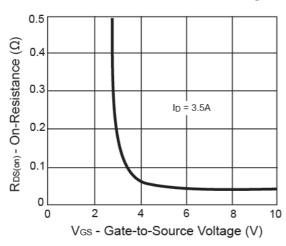
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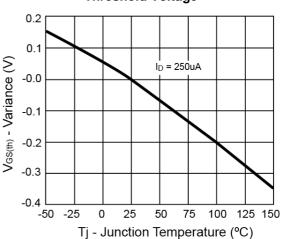


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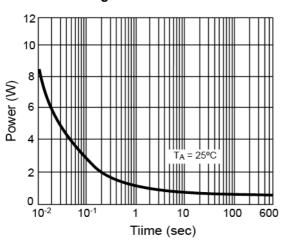
On-Resistance vs. Gate-Source Voltage



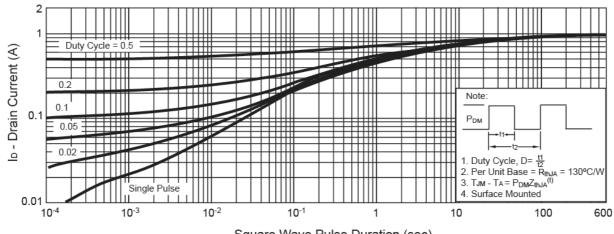
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



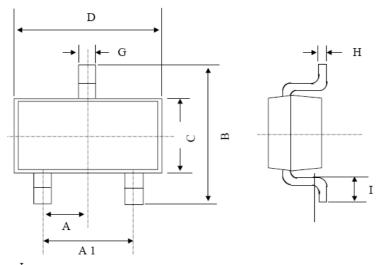




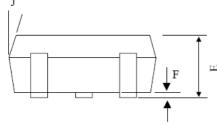


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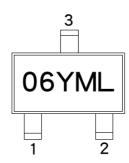
SOT-23 Mechanical Drawing



	SOT-23 DIMENSION					
	MILLIMETERS		INCHES			
DIM	MIN	MAX	MIN	MAX.		
Α	0.95	BSC	0.037 BSC			
A1	1.9 [BSC	0.074 BSC			
В	2.60	3.00	0.102	0.118		
С	1.40	1.70	0.055	0.067		
D	2.80	3.10	0.110	0.122		
E	1.00	1.30	0.039	0.051		
F	0.00	0.10	0.000	0.004		
G	0.35	0.50	0.014	0.020		
Н	0.10	0.20	0.004	0.008		
I	0.30	0.60	0.012	0.024		
J	5°	10°	5°	10°		



Marking Diagram



06 = Device Code

Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S =May T =Jun U =Jul V =Aug

W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code



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